

	U	T	Inventor	Document No.	P	Title	Current	Current XR	Retrieval	S/C	P	Image Doc.	P
1	C	C	Park, Il-Yong	US 2004021,2004:1		Method of manufacturing MOS transistor ha	439/197,438/589,			F	C	C	US 2004021
2	C	C	Park, Il-Yong	US 2004008,2004:1		MOS transistor having short channel and ma	257/327,257/328,			F	C	C	US 2004008
3	C	C	Tanigami, Ta	US 2002017,2002:4		Process for manufacturing semiconductor m	439/263,257/E21.68			F	C	C	US 2002017
4	C	C	Lin, Bih-Tiao	US 2002013,2002:7		Fabrication method of shallow trench isolatio	439/424,257/E21.54			F	C	C	US 2002013
5	C	C	Tanigami, Ta	US 6589844,2003:4		Process for manufacturing semiconductor de	439/261,257/E21.68			F	C	C	US 6589844
6	C	C	Tanigami, Ta	US 6441430,2002:4		Semiconductor device with floating gates	257/317,257/315,			F	C	C	US 6441430
7	C	C	Sakao, Masa	US 6228170,2001:1		Semiconductor memory cell	257/286,257/306,			F	C	C	US 6228170
8	C	C	Masuko, Sa	US 5994743,1999:1		Semiconductor device having different side	257/389,257/900,			F	C	C	US 5994743
9	C	C	Wu, Der-Yuan	US 5854106,1998:1		Method of forming a data storage capacitor	439/253,257/E21.64			F	C	C	US 5854106
10	C	C	Sun, Yi-Lin et	US 5834346,1998:1		Procedure for eliminating bubbles formed dur	439/231,257/E21.24			F	C	C	US 5834346